

Attorney's Docket No. 42390P5769

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Gang Bai

Serial No. 09/109,261

Filed: June 30, 1998

For: A MULTI-LAYER GATE DIELECTRIC

Examiner: Warren, M.

Art Group: 2815

J. McMillan

11/19/02

entered  
J. McMillan  
1/3/03

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TECHNOLOGY CENTER 2800

Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington, D.C. 20231AMENDMENT AND RESPONSE TO FINAL OFFICE ACTION

Dear Sir:

In response to the Final Office Action mailed September 10, 2002, in connection with the above referenced patent application, the Applicant respectfully requests entry of the following amendment and requests reconsideration in view of the following remarks. Entry is requested.

IN THE CLAIMS

Please cancel claims 11 and 18.

Presented below are all the amended claims in clean unmarked form. The claims, in marked-up form, are presented as an attachment.

8. (Five Times Amended) A transistor device having a gate electrode overlying a gate dielectric formed directly on a semiconductor substrate, the gate dielectric comprising:  
a first dielectric material having a first dielectric constant; and

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